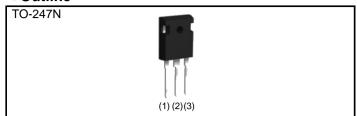


# RGS80TSX2HR

## 1200V 40A Field Stop Trench IGBT

V <sub>CES</sub>	1200V
I <sub>C (100°C)</sub>	40A
V <sub>CE(sat) (Typ.)</sub>	1.7V
$P_D$	555W

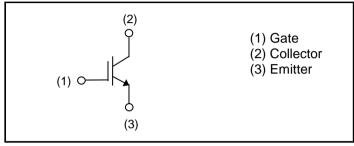
### Outline



### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 10µs
- 3) Qualified to AEC-Q101
- 4) Pb free Lead Plating; RoHS Compliant

### ●Inner Circuit



### Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Type	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGS80TSX2

## Application

Heater for Automotive

## ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

<b>5</b> \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \				
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	1200	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	80	А
	T <sub>C</sub> = 100°C	I <sub>C</sub>	40	А
Pulsed Collector Current		I <sub>CP</sub> *1	120	А
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	555	W
	T <sub>C</sub> = 100°C	P <sub>D</sub>	277	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax.</sub>

### ●Thermal Resistance

Parameter	Symbol	Values			Unit
raidilletei	Зупівої	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.27	°C/W

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Unit		
1 drameter	r drameter Symbol Conditions		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	1200	ı	1	V
		$V_{CE} = 1200V, V_{GE} = 0V,$				
Collector Cut - off Current	I <sub>CES</sub>	$T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C^{*2}$	-	-	10	μΑ
		Tj = 175°C <sup>*2</sup>	1	3	1	mA
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	1	ı	±500	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 6.1mA$	5.0	6.0	7.0	V
		$I_C = 40A, V_{GE} = 15V,$				
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	T <sub>j</sub> = 25°C	-	1.70	2.10	V
		T <sub>j</sub> = 175°C	-	2.20	-	V

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		L bade		
			Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	$V_{CE} = 30V$ ,	-	2820	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$ ,	-	161	-	pF
Reverse transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	25	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 500V,	-	104	-	
Gate - Emitter Charge	$Q_{ge}$	$I_{\rm C} = 40A$ ,	-	25	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	42	-	
Turn - on Delay Time	t <sub>d(on)</sub>		-	49	-	
Rise Time	t <sub>r</sub>	$I_C = 40A$ , $V_{CC} = 600V$ ,	-	27	-	
Turn - off Delay Time	t <sub>d(off)</sub>	$V_{GE} = 15V, R_G = 10\Omega,$ $T_i = 25^{\circ}C$	-	199	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	227	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> include diode reverse recovery	-	3.00	-	mJ
Turn - off Switching Loss	E <sub>off</sub>	,	-	3.10	-	
Turn - on Delay Time	t <sub>d(on)</sub>		-	49	-	
Rise Time	t <sub>r</sub>	$I_C = 40A, V_{CC} = 600V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	40	-	ns
Turn - off Delay Time	t <sub>d(off)</sub>	$V_{GE} = 15V, R_G - 10\Omega,$ $T_i = 175^{\circ}C$	ı	258	ı	
Fall Time	t <sub>f</sub>	Inductive Load	-	371	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> include diode reverse recovery	ı	3.80	ı	mJ
Turn - off Switching Loss	E <sub>off</sub>	·	•	4.50	-	1113
Reverse Bias Safe Operating Area	RBSOA	$I_C = 120A$ , $V_{CC} = 1050V$ , $V_P = 1200V$ , $V_{GE} = 15V$ , $R_G = 50\Omega$ , $T_j = 175$ °C	FULL SQUARE			-
Short Circuit Withstand Time	t <sub>sc</sub>	$V_{CC} \le 600V$ , $V_{GE} = 15V$ , $T_j = 25^{\circ}C$	10	-	-	μs
Short Circuit Withstand Time	t <sub>sc</sub> *2	$V_{CC} \le 600V$ , $V_{GE} = 15V$ , $T_j = 150$ °C	8	-	-	μs

<sup>\*2</sup> Design assurance without measurement

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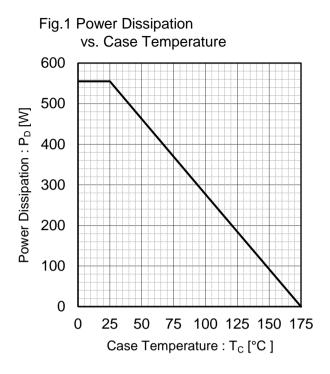


Fig.2 Collector Current vs. Case Temperature 100 80 Collector Current : Ic [A] 60 40 20 T<sub>i</sub> ≤ 175°C , G<sub>E</sub> ≥ 15V 0 25 75 100 125 150 175 0 Case Temperature : T<sub>C</sub> [°C]

Fig.3 Forward Bias Safe Operating Area 1000 10µs 100 Collector Current : I<sub>C</sub> [A] 10 100µs 1 0.1 T<sub>C</sub> = 25°C Single Pulse 0.01 10 100 1000 10000 Collector To Emitter Voltage: V<sub>CE</sub> [V]

140 120 Collector Current : Ic [A] 100 80 60 40 20 T<sub>i</sub> ≤ 175°C <sub>GE</sub> = 15V 0 0 400 800 1200 1600 Collector To Emitter Voltage : V<sub>CE</sub> [V]

Fig.4 Reverse Bias Safe Operating Area

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Fig.5 Typical Output Characteristics

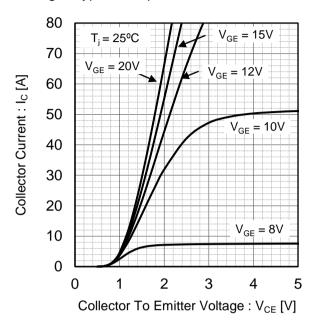


Fig.6 Typical Output Characteristics

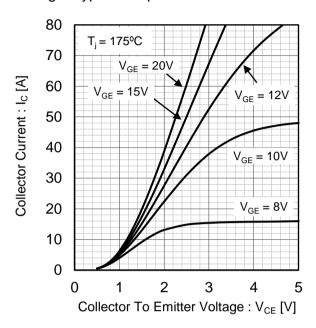


Fig.7 Typical Transfer Characteristics

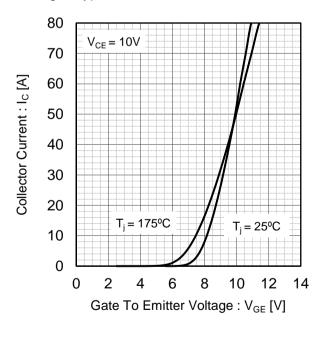
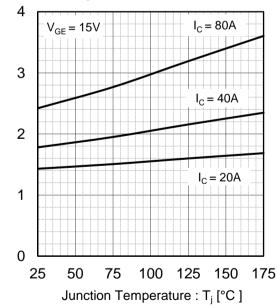


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



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Collector To Emitter Saturation Voltage

:  $V_{CE(sat)}[V]$ 

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

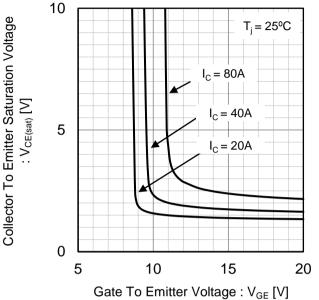


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

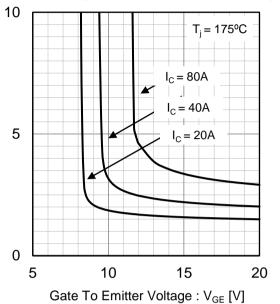


Fig.11 Typical Switching Time vs. Collector Current

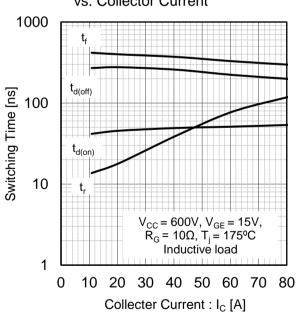
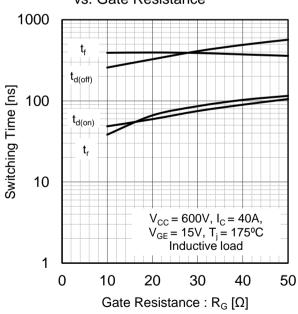


Fig.12 Typical Switching Time vs. Gate Resistance



Collector To Emitter Saturation Voltage

: V<sub>CE(sat)</sub> [V]

Fig.13 Typical Switching Energy Losses vs. Collector Current

100  $E_{off}$   $V_{CC} = 600V, V_{GE} = 15V, R_G = 10\Omega, T_j = 175^{\circ}C Inductive load

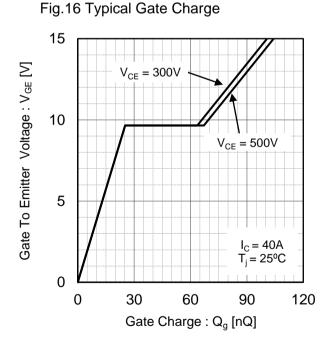
0.1

0 10 20 30 40 50 60 70 80

Collector Current : <math>I_C$  [A]

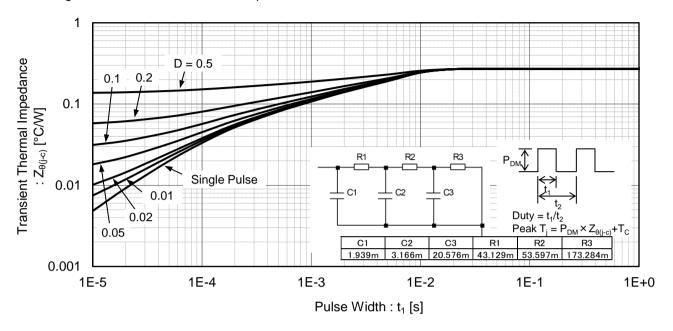
Fig.14 Typical Switching Energy Losses vs. Gate Resistance 100 Switching Energy Losses [mJ] 10  $\mathsf{E}_{\mathsf{off}}$ Eon 1  $V_{CC}$  = 600V,  $I_{C}$  = 40A,  $V_{GE}$  = 15V,  $T_{j}$  = 175°C Inductive load 0.1 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF]  $C_{\text{oes}}$ 100 10  $\mathsf{C}_{\mathsf{res}}$ f = 1MHz $V_{GE} = 0V$ T<sub>i</sub> = 25°C 1 0.01 0.1 1 10 100 Collector To Emitter Voltage: V<sub>CE</sub> [V]



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Fig.17 IGBT Transient Thermal Impedance



## ●Inductive Load Switching Circuit and Waveform

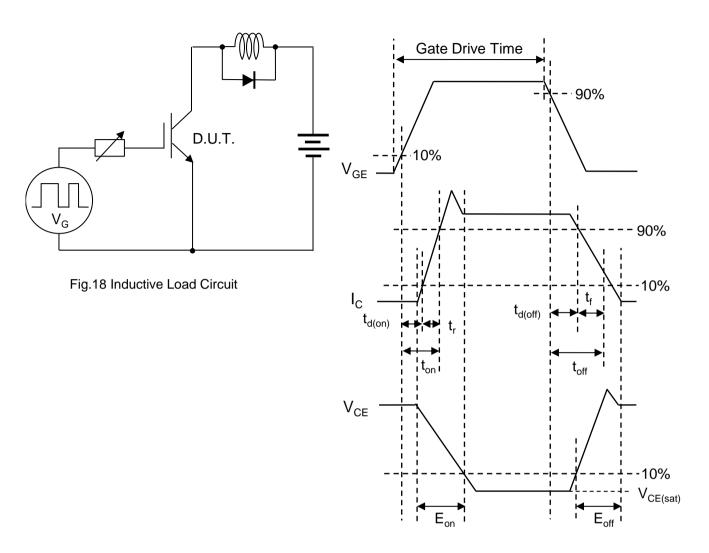


Fig.19 Inductive Load Waveform

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